

Octal 3-State Non-Inverting Buffer / Line Driver / Line Receiver in bare die form

Rev 1.1 01/05/18

Description

The 74HC244 is fabricated using a 2.5 μ m 5V CMOS process and has the same high speed performance of LSTTL combined with CMOS low power consumption. The device can be used as two 4-bit buffers or one 8-bit buffer and features non-inverting inputs with two output enables, each controlling four of the 3-state outputs. The device is specifically designed to improve performance and density in clock drivers, 3-state memory address drivers and bus orientated transmitters and receivers. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}

Ordering Information

The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product please see

54HC244

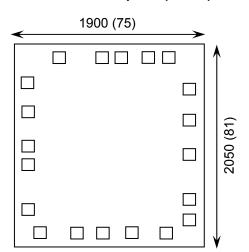
Supply Formats:

- Defact Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Features:

- Output Drive Capability: 15 LSTTL Lyads
- Low Input Current: 1µA
- Outputs directly interface CNCS NMOS and TTL
- Operating Voltage Range: 2% to 6V
- CMOS High Noise Impunity
- Function compatible with 74LS244.

Die Diplensions in µm (mils)



Mechanical Specification

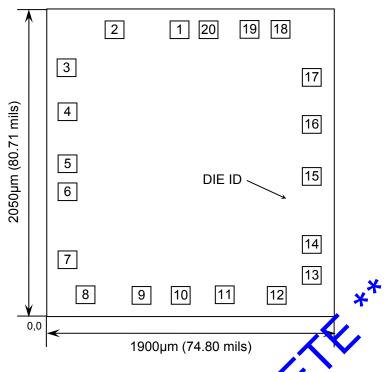
Die Size (Unsawn)	1900 x 2050 µr		
,	75 x 81	mils	
Minimum Bond Pad Size	100 x 100	μm	
wiii iii iii ii bonu Fau Size	3.94 x 3.94	mils	
Dio Thiokness	350 (±20)	μm	
Die Thickness	13.78 (±0.79)	mils	
Top Metal Composition	Al 1%Si 1.1μm		
Back Metal Composition	N/A – Bare Si		





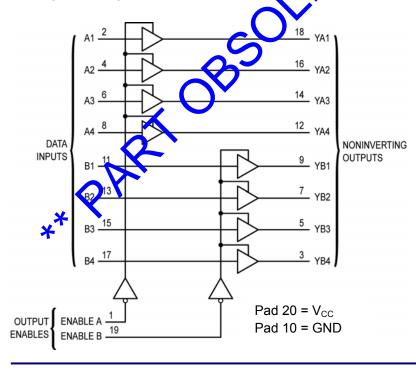
Rev 1.1 01/05/18

Pad Layout and Functions



PAD 1 2 3 4 5 YB3 А3 YB2 A4 YB1 **GND** 11 В1 12 YA4 13 B2 14 YA3 15 В3 YA2 16 B4 17 YA1 18 19 **ENABLE B** 20 V_{CC} CONNECT CHIP BACK TO V_{CC} OR FLOAT

Logic Diagram



Truth Table

INP	JTS	OUTPUTS
ENABLE A ENABLE B	A, B	YA, YB
L	L	L
L	Н	Н
H	X	Z

H = High level (steady state)

L = Low level (steady state)

X = Don't care

Z = High impedance





Rev 1.1 01/05/18

Pad Descriptions

ADDRESS INPUTS A1, A2, A3, A4, B1, B2, B3, B4 (Pads 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in non-inverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROL INPUTS

Enable A, Enable B (Pads 1, 19)

Output enables (active—low). When a low level is applied to these pins, the outputs are enabled and the delices function as non-inverting buffers. When a high level is applied, the outputs assume the high impedance state.

OUTPUTS

YA1, YA2, YA3, YA4, YB1, YB2, YB3, YB4 (Pads 18, 16, 14, 12, 9, 7, 5, 3)

Device outputs. Depending upon the state of the output- enable pins, these outputs are either non-inverting outputs or high-impedance outputs.

Absolute Maximum Ratings¹

9			
PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V _{CC}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	¥ V _{IN}	-1.5 to V _{CC} +1.5	V
DC Output Voltage (Referenced to GND)	V _{OUT}	-0.5 to V _{CC} +0.5	V
DC Input Current, per pin	I _{IN}	±20	mA
DC Output Current, per pin	I _{OUT}	±35	mA
DC V _{CC} or GND Current, per pin	I _{CC}	±75	mA
Power Dissipation in Still Air ²	P _D	750	mW
Storage Temperature Range	T _{STG}	-65 to 150	°C

^{1.} Operation above the absolute maximum ating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in pastic DV package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions³ (Voltages referenced to GND)

PARAMETER	SYMBOL	MIN	MAX	UNITS	
DC Supply Voltage	V _{CC}	2	6	V	
DC Input or Optput Voltage	V_{IN} , V_{OUT}	0	V _{CC}	V	
Operating 16 my erature Ran	T _A	0	+85	°C	
	V _{CC} = 2.0V		0	1000	ns
Input Rise and Fall Time	V _{CC} = 4.5V	t _r , t _f	0	500	
_	V _{CC} = 6.0V		0	400	

^{3.} This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND \leq (V_{IN} or V_{OUT}) \leq V_{CC} . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.





Rev 1.1 01/05/18

DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	V _{cc} COND	CONDITIONS		LIMITS		
TANAMETER	OTHIDOL	▼ CC	CONDITIONS	25°C	85°C	FULL RANGE	UNITS
		2.0V		1.5	1.5	1.5	
Minimum High-Level	V _{IH}	3.0V	$V_{OUT} = V_{CC} - 0.1V$	2.1	2.1	21	$\ $ \vee
Input Voltage	V IH	4.5V	I _{OUT} ≤ 20μA	3.15	3.15	7.10	
		6.0V		4.2	4.2	4.2	
		2.0V	.,	0.5	0.5	0.5	
Maximum Low-Level	V _{IL}	3.0V	$V_{OUT} = 0.1V$ $\left I_{OUT} \right \le 20\mu A$	0.9	0.0	0.9	V
Input Voltage	V 1L	4.5V	1001 = 20μΛ	1.35	.35	1.35	
		6.0V		1.8	1.8	1.8	
		2.0V	$V_{IN} = V_{IH}$	1.9	1.9	1.9	
		4.5V	$ I_{OUT} \le 20 \mu A$	4.4	4.4	4.4	V
		6.0V	1 0011 -1	5.9	5.9	5.9	
Minimum High-Level Output Voltage	V _{OH}	3.0V	$V_{IN} = V_{IH}$ $\left I_{OUT} \right \le 2.4 \text{mA}$	2.48	2.34	2.34	V
, ,		4.5V	$V_{IN} = V_{IA}$ $ I_{OUT} \le 6.0 \text{mA}$	3.98	3.84	3.84	
		6.0V	VIN ₹ VINI ONT ≤ V.8mA	5.48	5.34	5.34	
		2.0V		0.1	0.1	0.1	
	V _{OL} 3	4.5V	$V_{IN} = V_{IL}$ $I_{OUT} \le 20\mu A$	0.1	0.1	0.1	V
		6.UV		0.1	0.1	0.1	
Maximum Low-Level Output Voltage		300	$V_{IN} = V_{IL}$ $\left I_{OUT} \right \le 2.4 \text{mA}$	0.26	0.33	0.33	
, ,		4.5V	$V_{IN} = V_{IL}$ $\left I_{OUT} \right \le 6.0 \text{mA}$	0.26	0.33	0.33	V
		6.0V	$V_{IN} = V_{IL}$ $\left I_{OUT} \right \le 7.8 \text{mA}$	0.26	0.33	0.33	
Maximum Input Leakage Current	I _{IN}	6.0V	$V_{IN} = V_{CC}$ or GND	±0.1	±1.0	±1.0	μA
Maximum 3-State leakage current	I _{OZ}	6.0V	$V_{OUT} = V_{CC} \text{ or } 0$ $V_{IN} = V_{IL} \text{ or } V_{IH}$	±0.5	±5.0	±5.0	μA
Maximum Quiescent Supply Leakage Current	I _{cc}	6.0V	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$	4	40	40	μА

^{4.} $0^{\circ}C \le T_{J} \le +85^{\circ}C$





AC Electrical Characteristics⁵

Rev 1.1 01/05/18

PARAMETER	SYMBOL	V _{cc} CONDITIONS	LIMITS			WITS	
			CONDITIONS	25°C	85°C	FULL RANGE	
Maximum Propagation Delay,	t _{PLH} , t _{PHL}	2.0V		96	115	115	ns
		3.0V	C _L = 50pF,	50	60	60	
A to YA or B to YB	PLH, PHL	4.5V	$t_r = t_f = 6$ ns	18	23	28	113
(Figure 1, 3)		6.0V		15	20	20	
Maximum Propagation		2.0V		110	140	140	ns
Delay,	t _{PLZ} , t _{PHZ}	3.0V	$C_L = 50pF$,	60	70	70	
Output Enable to YA or YB	PLZ, PHZ	4.5V	$t_r = t_f = 6$ ns	22	28	28	
(Figure 2,4)		6.0V	6.0V	19	24	24	
Maximum Propagation		2.0V	$C_L = 50pF,$ $t_r = t_f = 6ns$	110	40	140	ns
Delay,		3.0		60	70	70	
Output Enable to YA or YB	t _{PZL} , t _{PZH}	4.5V		22	28	28	
(Figure 2,4)		6.0V		13	24	24	
		2.0V	•	60	75	75	ns
Maximum Output Rise and Fall Time (Figure 1, 3)	t _{TLH} , t _{THL}	3.0V	$C_{L} = 50 \text{ pF},$ $t_{r} = t_{f} = 6 \text{ ns}$	23	27	27	
		4.5V		12	15	15	
		6.0V		10	13	13	
Maximum Input Capacitance	C _{IN}	- (-	10	10	10	pF
Maximum Three-State Output Capacitance (Output in High- Impedance State)	Соит		-	15	15	15	pF
Power Dissipation Capacitance (Per Buffer) ⁵	PD	-	$T_A = 25^{\circ}C$, $V_{CC} = 5.0V$		TYPIC 34	AL	pF

 ^{5.} Not production tested in die form, characterized by chip design and tested in package LAT.
 6. Used to determine the local dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}.





Rev 1.1 01/05/18

Switching Waveforms

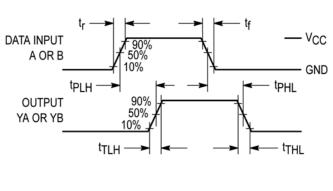
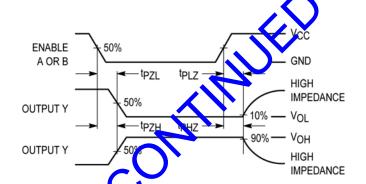
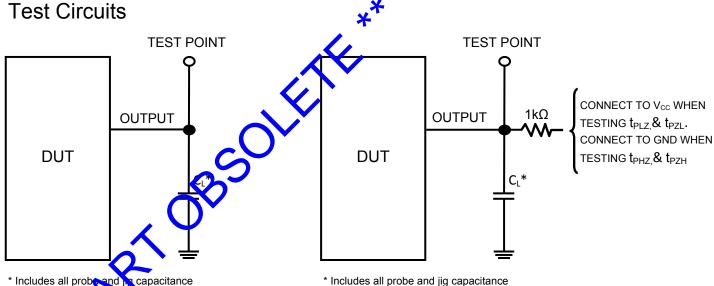


Figure 1 - Propagation Delay Input A or B to Output YA or YB



e 2 – Propagation Delay utput Enable to Output YA or YB



* Includes all proband in capacitance

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Figure 4

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